

阅读申明

- 1.本站收集的数据手册和产品资料都来自互联网，版权归原作者所有。如读者和版权方有任何异议请及时告之，我们将妥善解决。
- 2.本站提供的中文数据手册是英文数据手册的中文翻译，其目的是协助用户阅读，该译文无法自动跟随原稿更新，同时也可能存在翻译上的不当。建议读者以英文原稿为参考以便获得更精准的信息。
- 3.本站提供的产品资料，来自厂商的技术支持或者使用者的心得体会等，其内容可能存在描述上的差异，建议读者做出适当判断。
- 4.如需与我们联系，请发邮件到marketing@iczoom.com，主题请标有“数据手册”字样。

Read Statement

1. The datasheets and other product information on the site are all from network reference or other public materials, and the copyright belongs to the original author and original published source. If readers and copyright owners have any objections, please contact us and we will deal with it in a timely manner.
2. The Chinese datasheets provided on the website is a Chinese translation of the English datasheets. Its purpose is for reader's learning exchange only and do not involve commercial purposes. The translation cannot be automatically updated with the original manuscript, and there may also be improper translations. Readers are advised to use the English manuscript as a reference for more accurate information.
3. All product information provided on the website refer to solutions from manufacturers' technical support or users the contents may have differences in description, and readers are advised to take the original article as the standard.
4. If you have any questions, please contact us at marketing@iczoom.com and mark the subject with "Datasheets" .

Darlington Complementary Silicon Power Transistors

... designed for general-purpose amplifier and low frequency switching applications.

- High DC Current Gain —
 $h_{FE} = 3500$ (Typ) @ $I_C = 5.0$ Adc
- Collector–Emitter Sustaining Voltage — @ 100 mA
 $V_{CEO(sus)} = 80$ Vdc (Min) — 2N6058
 100 Vdc (Min) — 2N6052, 2N6059
- Monolithic Construction with Built–In Base–Emitter Shunt Resistors

MAXIMUM RATINGS (1)

Rating	Symbol	2N6058	2N6052 2N6059	Unit
Collector–Emitter Voltage	V_{CEO}	80	100	Vdc
Collector–Base Voltage	V_{CB}	80	100	Vdc
Emitter–Base voltage	V_{EB}	5.0		Vdc
Collector Current — Continuous Peak	I_C	12 20		Adc
Base Current	I_B	0.2		Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	150	0.857	Watts W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–65 to +200 $^\circ\text{C}$		$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Rating	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.17	$^\circ\text{C/W}$

(1) Indicates JEDEC Registered Data.

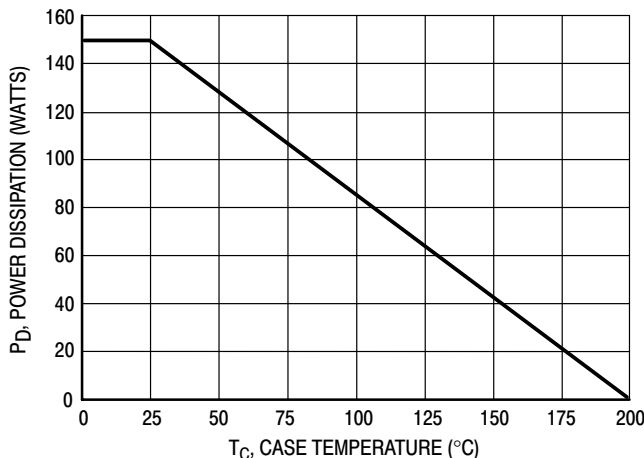


Figure 1. Power Derating

Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

PNP
2N6052*

NPN
2N6058
2N6059*

*ON Semiconductor Preferred Device

DARLINGTON
12 AMPERE
COMPLEMENTARY
SILICON
POWER TRANSISTORS
80–100 VOLTS
150 WATTS

CASE 1–07
TO–204AA
(TO–3)

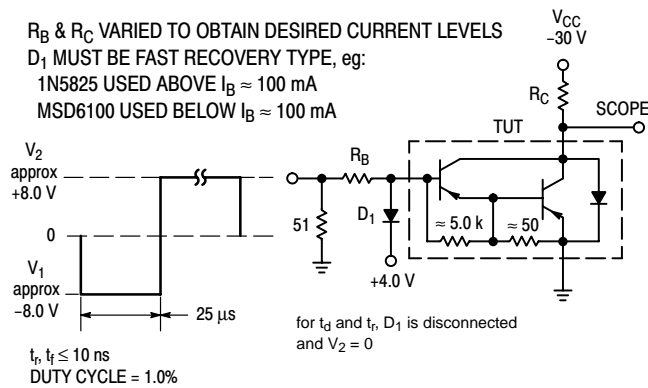
2N6052

*ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage (2) ($I_C = 100\text{ mAdc}$, $I_B = 0$)	$V_{CEO(sus)}$	80 100	—	Vdc
	2N6058 2N6052, 2N6059			
Collector Cutoff Current ($V_{CE} = 40\text{ Vdc}$, $I_B = 0$) ($V_{CE} = 50\text{ Vdc}$, $I_B = 0$)	I_{CEO}	—	1.0 1.0	mAdc
	2N6058 2N6052, 2N6059			
Collector Cutoff Current ($V_{CE} = \text{Rated } V_{CEO}$, $V_{BE(off)} = 1.5\text{ Vdc}$) ($V_{CE} = \text{Rated } V_{CEO}$, $V_{BE(off)} = 1.5\text{ Vdc}$, $T_C = 150^\circ\text{C}$)	I_{CEX}	—	0.5 5.0	mAdc
Emitter Cutoff Current ($V_{BE} = 5.0\text{ Vdc}$, $I_C = 0$)	I_{EBO}	—	2.0	mAdc
ON CHARACTERISTICS (2)				
DC Current Gain ($I_C = 6.0\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$) ($I_C = 12\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$)	h_{FE}	750 100	18,000 —	—
Collector–Emitter Saturation Voltage ($I_C = 6.0\text{ Adc}$, $I_B = 24\text{ mAdc}$) ($I_C = 12\text{ Adc}$, $I_B = 120\text{ mAdc}$)	$V_{CE(sat)}$	—	2.0 3.0	Vdc
Base–Emitter Saturation Voltage ($I_C = 12\text{ Adc}$, $I_B = 120\text{ mAdc}$)	$V_{BE(sat)}$	—	4.0	Vdc
Base–Emitter On Voltage ($I_C = 6.0\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$)	$V_{BE(on)}$	—	2.8	Vdc
DYNAMIC CHARACTERISTICS				
Magnitude of Common Emitter Small–Signal Short Circuit Forward Current Transfer Ratio ($I_C = 5.0\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$, $f = 1.0\text{ MHz}$)	$ h_{fe} $	4.0	—	MHz
Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 0.1\text{ MHz}$)	C_{ob}	—	500 300	pF
	2N6052 2N6058/2N6059			
Small–Signal Current Gain ($I_C = 5.0\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$, $f = 1.0\text{ kHz}$)	h_{fe}	300	—	—

*Indicates JEDEC Registered Data.

(2) Pulse test: Pulse Width = 300 μs , Duty Cycle = 2.0%.



For NPN test circuit reverse diode and voltage polarities.

Figure 2. Switching Times Test Circuit

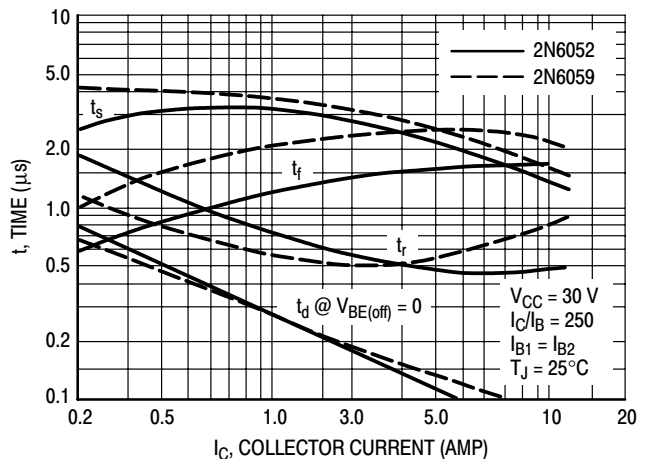


Figure 3. Switching Times

2N6052

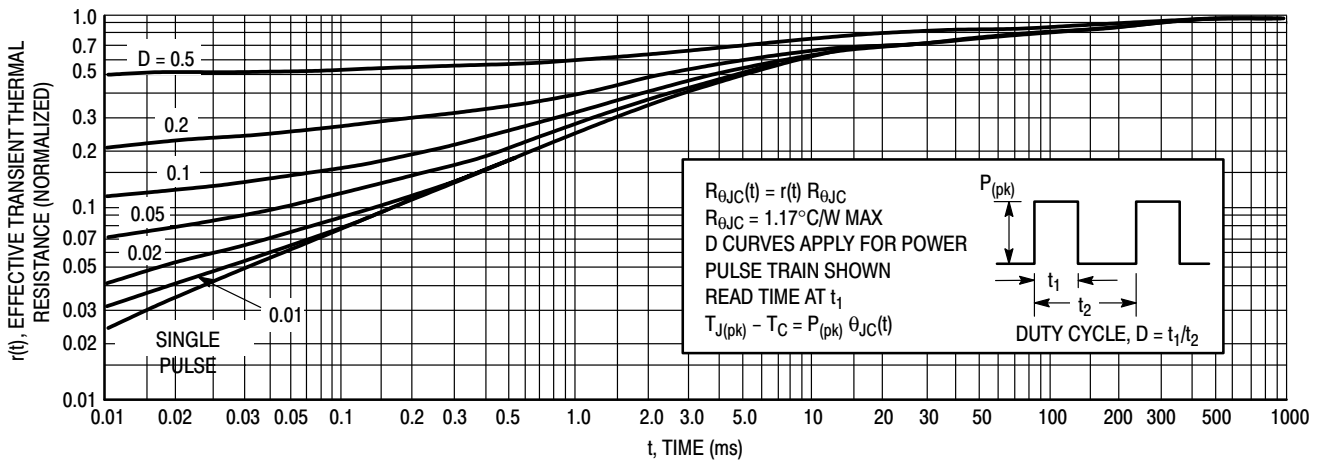


Figure 4. Thermal Response

ACTIVE-REGION SAFE OPERATING AREA

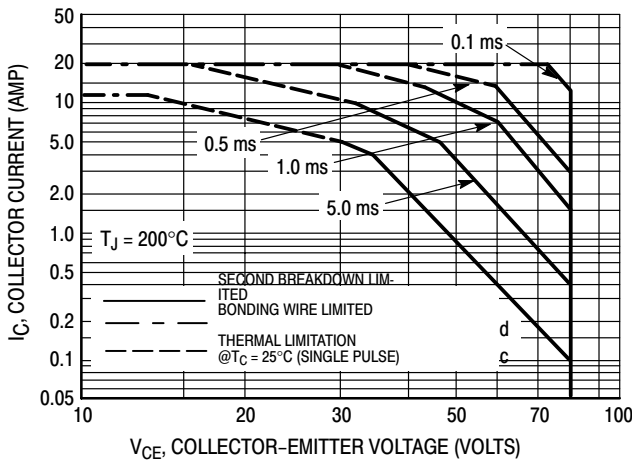


Figure 5. 2N6058

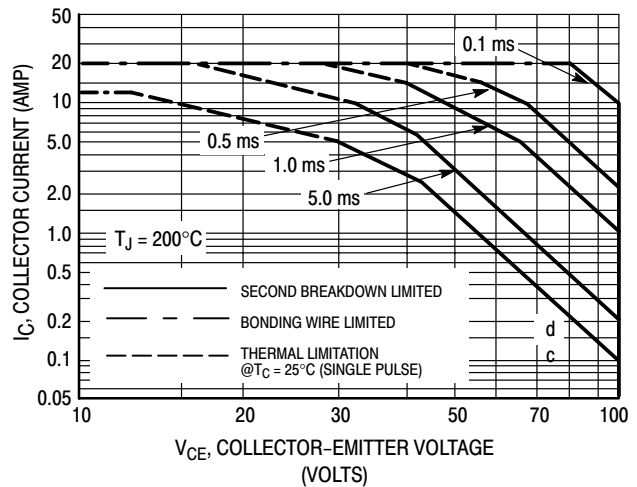


Figure 6. 2N6052, 2N6059

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figures 5, 6, and 7 is based on $T_{J(pk)} = 200^{\circ}\text{C}$; T_C is variable depending on conditions. Second breakdown

pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 200^{\circ}\text{C}$; $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

2N6052

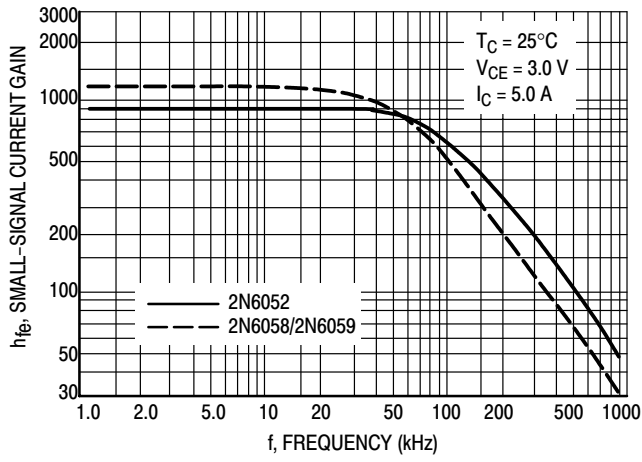


Figure 7. Small-Signal Current Gain

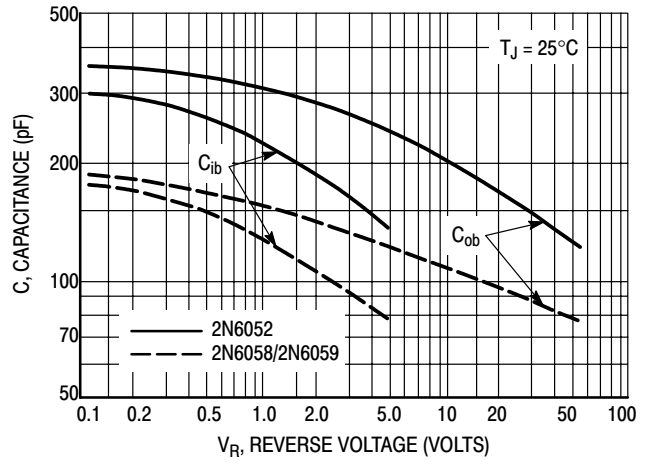


Figure 8. Capacitance

2N6052

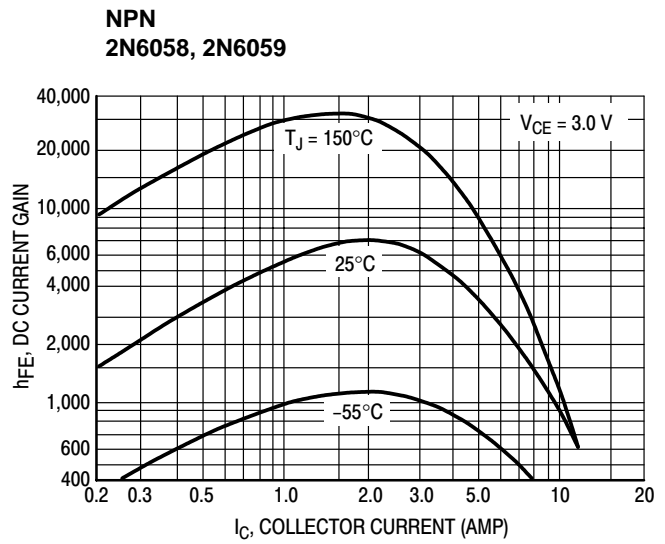
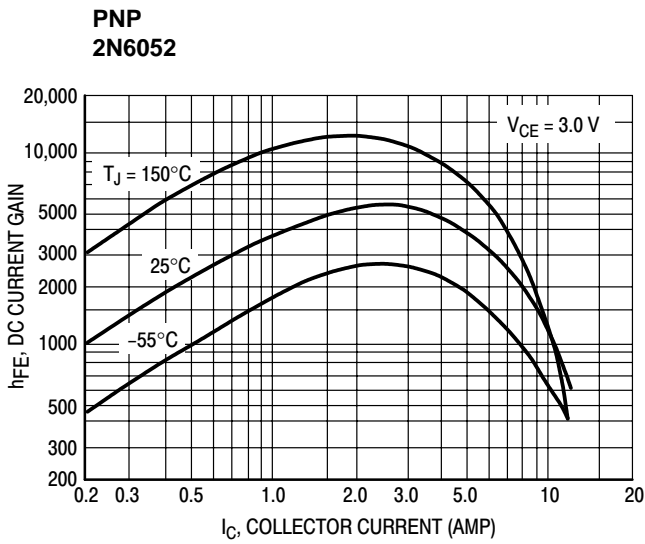


Figure 9. DC Current Gain

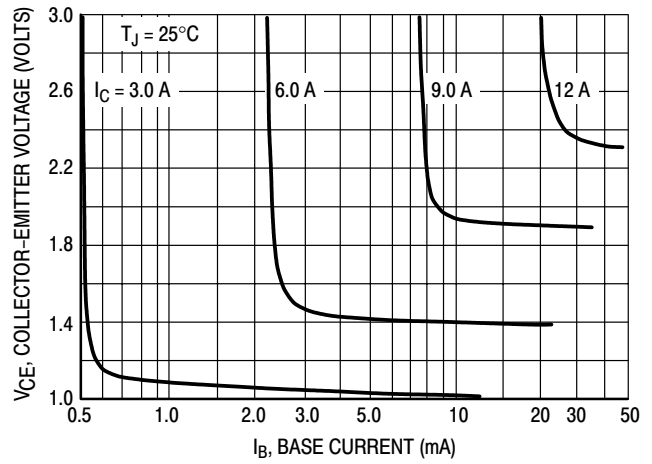
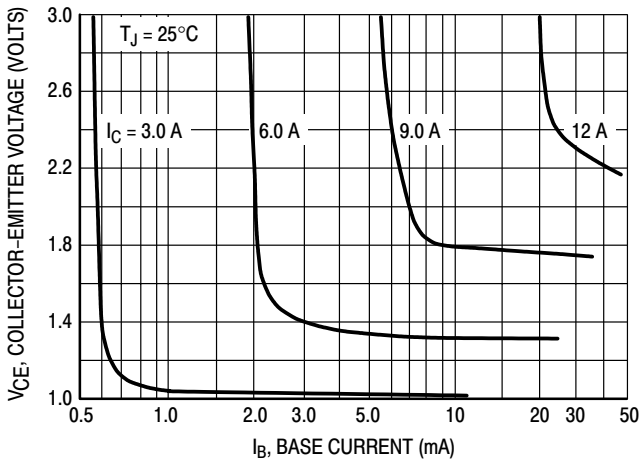


Figure 10. Collector Saturation Region

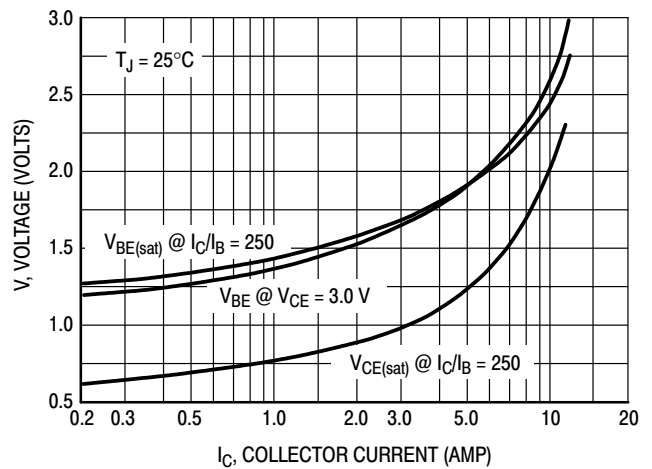
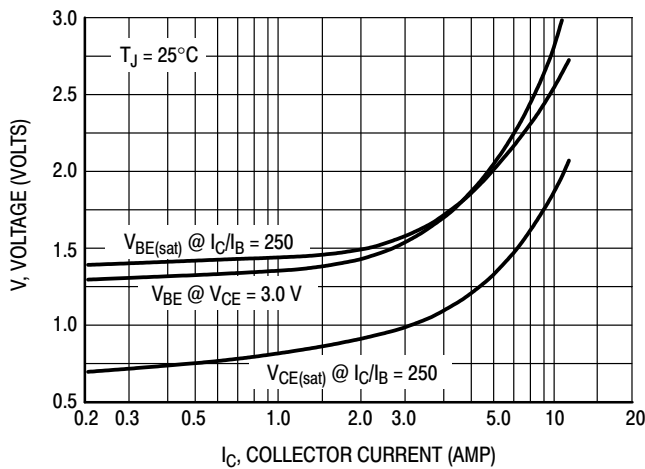
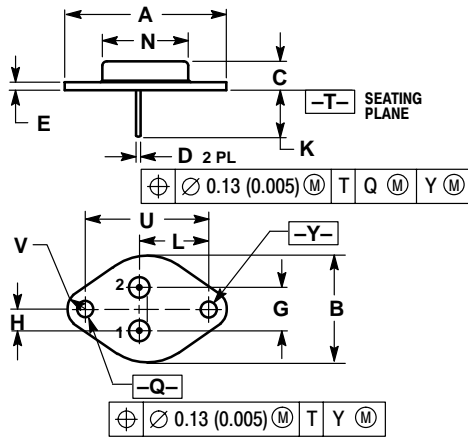


Figure 11. "On" Voltages

2N6052

PACKAGE DIMENSIONS

CASE 1-07 TO-204AA (TO-3) ISSUE Z




- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.550 REF		39.37 REF	
B	---	1.050	---	26.67
C	0.250	0.335	6.35	8.51
D	0.038	0.043	0.97	1.09
E	0.055	0.070	1.40	1.77
G	0.430 BSC		10.92 BSC	
H	0.215 BSC		5.46 BSC	
K	0.440	0.480	11.18	12.19
L	0.665 BSC		16.89 BSC	
N	---	0.830	---	21.08
Q	0.151	0.165	3.84	4.19
U	1.187 BSC		30.15 BSC	
V	0.131	0.188	3.33	4.77

STYLE 1:
PIN 1. BASE
2. EMITTER
CASE: COLLECTOR

Notes

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

PUBLICATION ORDERING INFORMATION

NORTH AMERICA Literature Fulfillment:

Literature Distribution Center for ON Semiconductor
 P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: ONlit@hibbertco.com
 Fax Response Line: 303-675-2167 or 800-344-3810 Toll Free USA/Canada

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

EUROPE: LDC for ON Semiconductor – European Support

German Phone: (+1) 303-308-7140 (Mon-Fri 2:30pm to 7:00pm CET)
Email: ONlit-german@hibbertco.com
French Phone: (+1) 303-308-7141 (Mon-Fri 2:00pm to 7:00pm CET)
Email: ONlit-french@hibbertco.com
English Phone: (+1) 303-308-7142 (Mon-Fri 12:00pm to 5:00pm GMT)
Email: ONlit@hibbertco.com

EUROPEAN TOLL-FREE ACCESS*: 00-800-4422-3781

*Available from Germany, France, Italy, UK, Ireland

CENTRAL/SOUTH AMERICA:

Spanish Phone: 303-308-7143 (Mon-Fri 8:00am to 5:00pm MST)
Email: ONlit-spanish@hibbertco.com
Toll-Free from Mexico: Dial 01-800-288-2872 for Access –
 then Dial 866-297-9322

ASIA/PACIFIC: LDC for ON Semiconductor – Asia Support

Phone: 1-303-675-2121 (Tue-Fri 9:00am to 1:00pm, Hong Kong Time)
Toll Free from Hong Kong & Singapore:
001-800-4422-3781
Email: ONlit-asia@hibbertco.com

JAPAN: ON Semiconductor, Japan Customer Focus Center

4-32-1 Nishi-Gotanda, Shinagawa-ku, Tokyo, Japan 141-0031
Phone: 81-3-5740-2700
Email: r14525@onsemi.com

ON Semiconductor Website: <http://onsemi.com>

For additional information, please contact your local Sales Representative.